



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jae-Hyun Ryou et al.

Serial No.: 10/607,758

Examiner: unknown

Filing Date: June 27, 2003

Group Art: unknown

For: VCSEL HAVING THERMAL MANAGEMENT

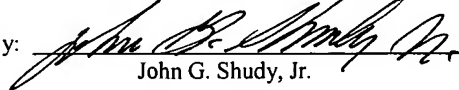
Docket No.: H0004788 (1139.1138101)

TRANSMITTAL SHEET

Assistant Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450


CERTIFICATE UNDER 37 C.F.R. 1.8: I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, on this 25th day of November, 2003.

By:


John G. Shudy, Jr.

We are transmitting herewith the attached:

- ☒ Information Disclosure Statement, Form PTO-1449 and 248 cited references.
☒ Please charge any deficiencies or credit any overpayment in the enclosed fees to Deposit Account No. 50-0413.


John G. Shudy, Jr., Reg. No. 31,214
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INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))

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By: 

John G. Shudy, Jr.

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F. R. §1.98(a)(2), a copy of each US patent or other information listed on the enclosed Form 1449 is provided.

No representation is intended to be made hereby that any of the cited references establishes, by itself or in combination with other information, a prima facie case of unpatentability of any claim of the present case.

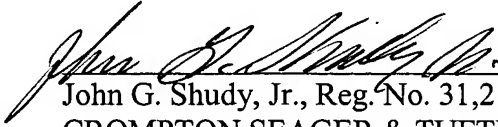
Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Respectfully submitted,

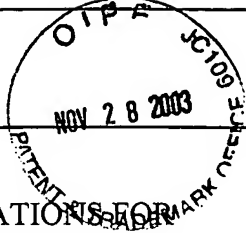
Jae-Hyun Ryou et al.

By their attorney,

Date: 11/25/03



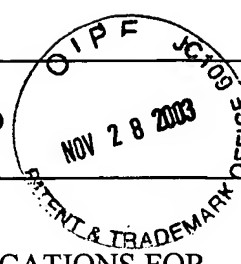
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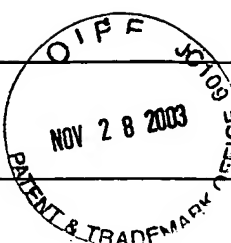
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	5,237,581	08/17/1993	Asada et al.			
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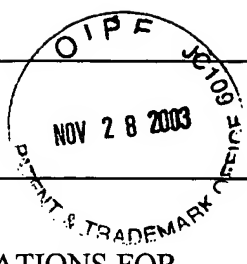
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	5,642,376	06/24/1997	Olbright et al.			
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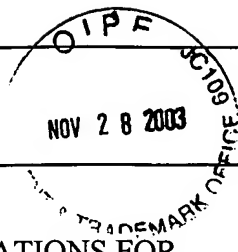
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		Filing Date: June 27, 2003	Group Art: unknown

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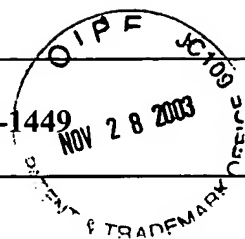
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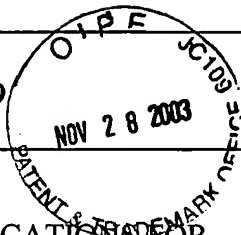
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✓	U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".
✓	U.S. Patent Application Serial No. 09/751,423, filed December 29, 2000, entitled "Spatially Modulated Reflector for an Optoelectronic Device".

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